

## N-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω) MAX.	I <sub>D</sub> (A)	Q <sub>g</sub> (TYP.)
100	0.00610 at V <sub>GS</sub> = 10 V	56.6	53.5 nC
	0.00700 at V <sub>GS</sub> = 7.5 V	54.4	

**Thin-Lead TO-220 FULLPAK**


**Ordering Information:**  
SUA70060E-E3 (lead (Pb)-free)

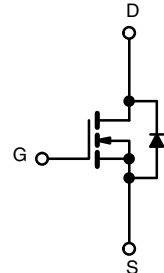
### FEATURES

- ThunderFET® power MOSFET
- Q<sub>gd</sub> / Q<sub>gs</sub> ratio < 1 optimizes switching characteristics
- 100 % R<sub>g</sub> and UIS tested
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)


**RoHS**  
COMPLIANT

### APPLICATIONS

- Power supply
  - Secondary synchronous rectification
  - AC/DC switch-mode power supplies
- DC/DC converter
- Power tools
- Motor drive switch
- DC/AC inverter



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V <sub>DS</sub>	100	V
Gate-Source Voltage		V <sub>GS</sub>	± 20	
Continuous Drain Current (T <sub>J</sub> = 150 °C)	T <sub>C</sub> = 25 °C	I <sub>D</sub>	56.6	A
	T <sub>C</sub> = 70 °C		45.2	
Pulsed Drain Current (t = 100 μs)		I <sub>DM</sub>	240	
Avalanche Current		I <sub>AS</sub>	50	
Single Avalanche Energy <sup>a</sup>	L = 0.1 mH	E <sub>AS</sub>	125	mJ
Maximum Power Dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	P <sub>D</sub>	39	W
	T <sub>C</sub> = 70 °C		25	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient (PCB Mount) <sup>b</sup>		R <sub>thJA</sub>	60	°C/W
Junction-to-Case (Drain)		R <sub>thJC</sub>	3.2	

### Notes

- Duty cycle ≤ 1 %.
- When mounted on 1" square PCB (FR4 material).



SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	100	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2	-	4	
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V	-	-	± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V	-	-	1	μA
		V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C	-	-	100	
		V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 150 °C	-	-	2	mA
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ 10 V, V <sub>GS</sub> = 10 V	50	-	-	A
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 30 A	-	0.00505	0.00610	Ω
		V <sub>GS</sub> = 7.5 V, I <sub>D</sub> = 20 A	-	0.00540	0.00700	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 30 A	-	85	-	S
<b>Dynamic <sup>b</sup></b>						
Input Capacitance	C <sub>ISS</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 50 V, f = 1 MHz	-	3300	-	pF
Output Capacitance	C <sub>OSS</sub>		-	1395	-	
Reverse Transfer Capacitance	C <sub>RSS</sub>		-	95	-	
Total Gate Charge <sup>c</sup>	Q <sub>g</sub>	V <sub>DS</sub> = 50 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 30 A	-	53.5	81	nC
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>		-	14.5	-	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>		-	13.2	-	
Gate Resistance	R <sub>g</sub>	f = 1 MHz	0.9	1.9	3.8	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>	V <sub>DD</sub> = 50 V, R <sub>L</sub> = 1.67 Ω I <sub>D</sub> ≅ 30 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 1 Ω	-	13	26	ns
Rise Time <sup>c</sup>	t <sub>r</sub>		-	22	44	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>		-	27	54	
Fall Time <sup>c</sup>	t <sub>f</sub>		-	9	18	
<b>Drain-Source Body Diode Ratings and Characteristics <sup>b</sup> (T<sub>C</sub> = 25 °C)</b>						
Pulsed Current (t = 100 μs)	I <sub>SM</sub>		-	-	240	A
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>F</sub> = 30 A, V <sub>GS</sub> = 0 V	-	0.86	1.4	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 30 A, di/dt = 100 A/μs	-	88	178	ns
Peak Reverse Recovery Charge	I <sub>RM(REC)</sub>		-	5	10	A
Reverse Recovery Charge	Q <sub>rr</sub>		-	220	440	nC

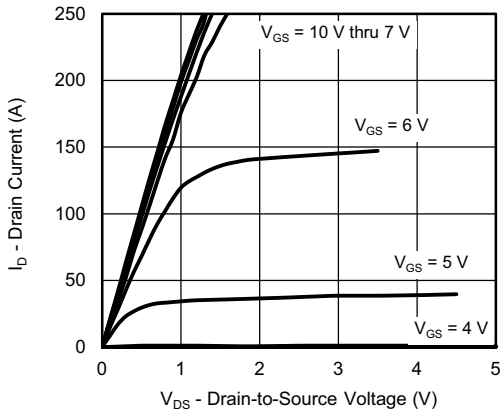
**Notes**

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.  
b. Guaranteed by design, not subject to production testing.  
c. Independent of operating temperature.

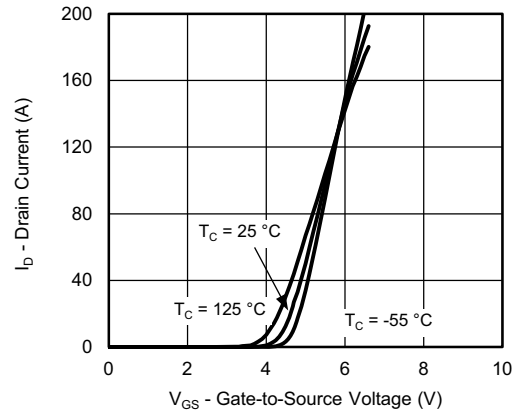
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



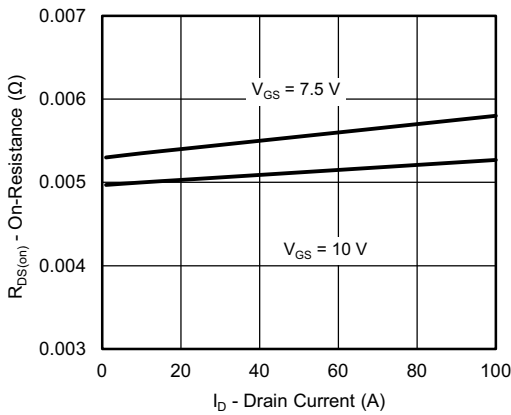
TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



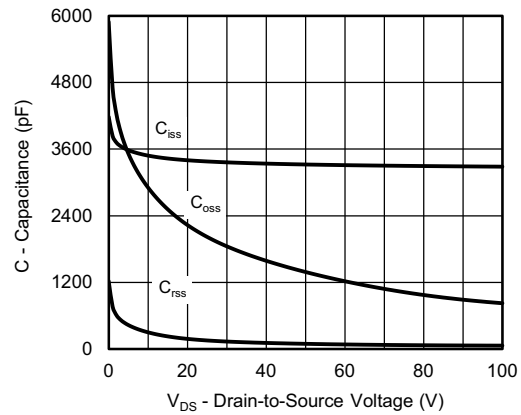
Output Characteristics



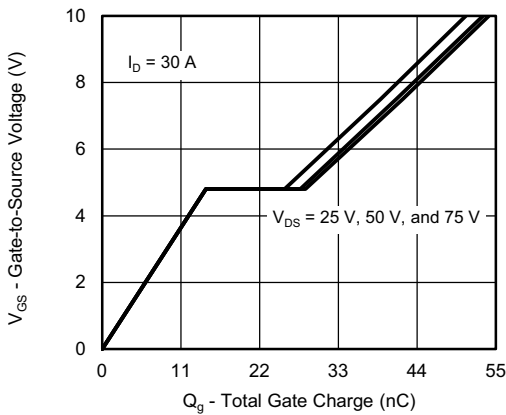
Transfer Characteristics



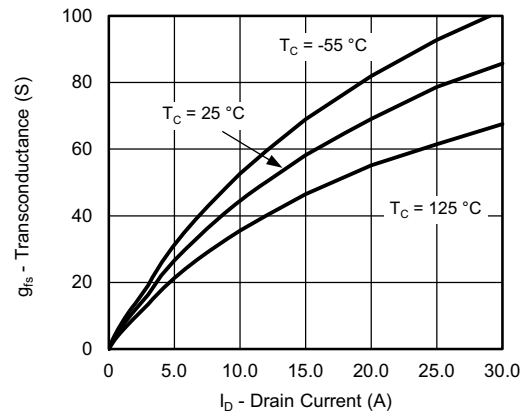
On-Resistance vs. Drain Current



Capacitance

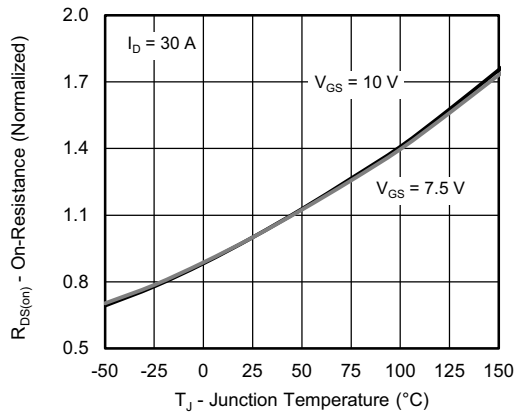


Gate Charge

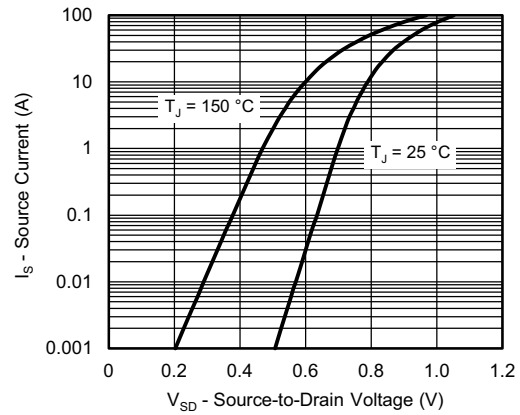


Transconductance

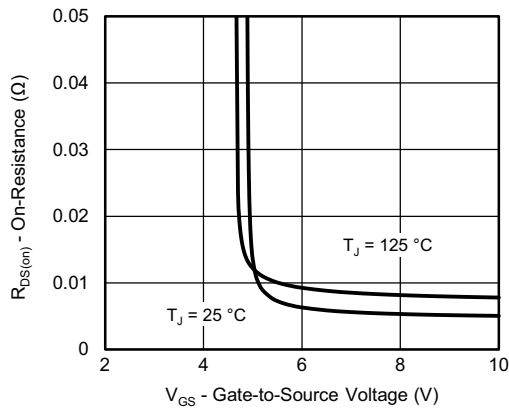
**TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



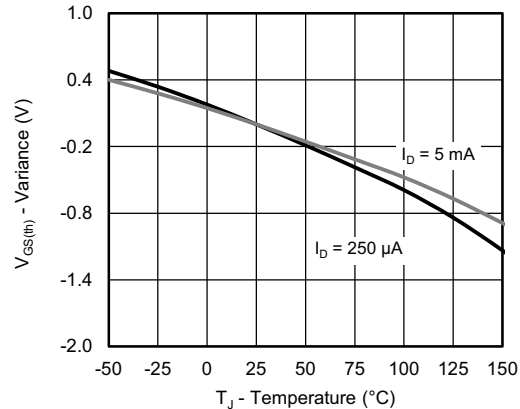
**On-Resistance vs. Junction Temperature**



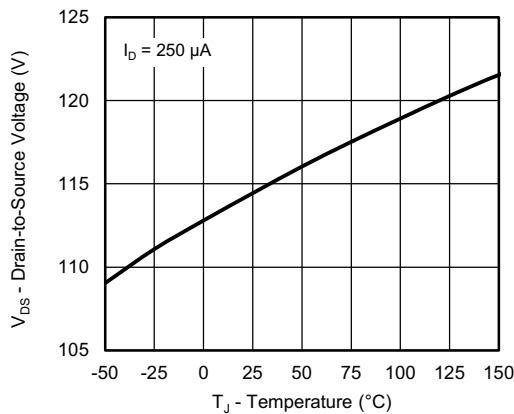
**Source Drain Diode Forward Voltage**



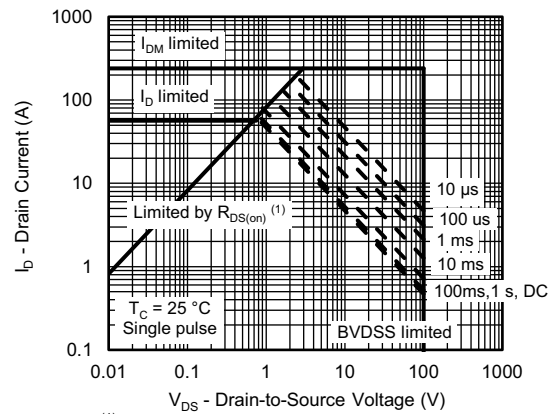
**On-Resistance vs. Gate-to-Source Voltage**



**Threshold Voltage**



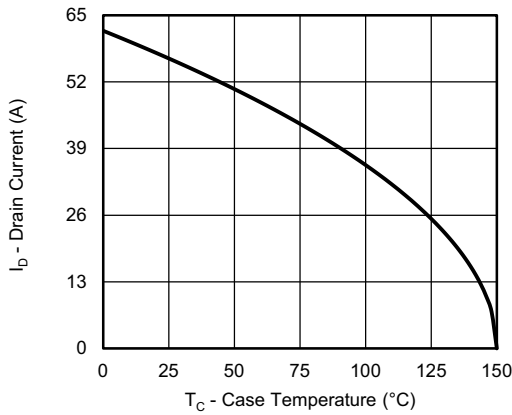
**Drain Source Voltage vs. Junction Temperature**



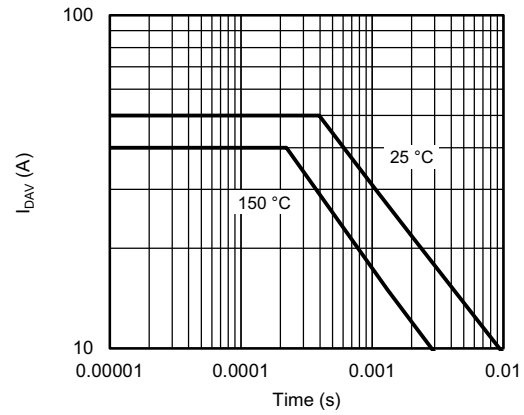
**Safe Operating Area**



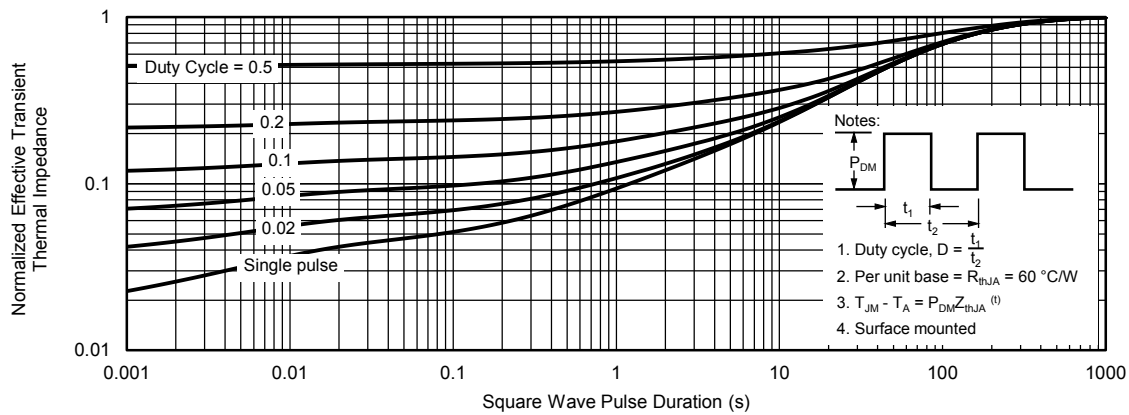
**THERMAL RATINGS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



**Current De-Rating**



**$I_{DAV}$  vs. Time**



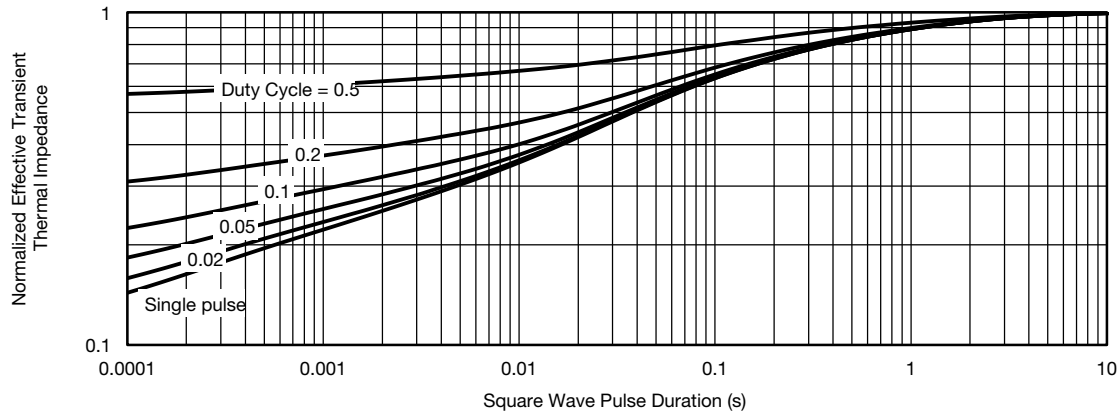
**Normalized Thermal Transient Impedance, Junction-to-Ambient**

**Note**

- The characteristics shown in the two graphs
    - Normalized Transient Thermal Impedance Junction to Ambient (25  $^\circ\text{C}$ )
    - Normalized Transient Thermal Impedance Junction to Case (25  $^\circ\text{C}$ )
- are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.



**THERMAL RATINGS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)

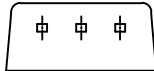
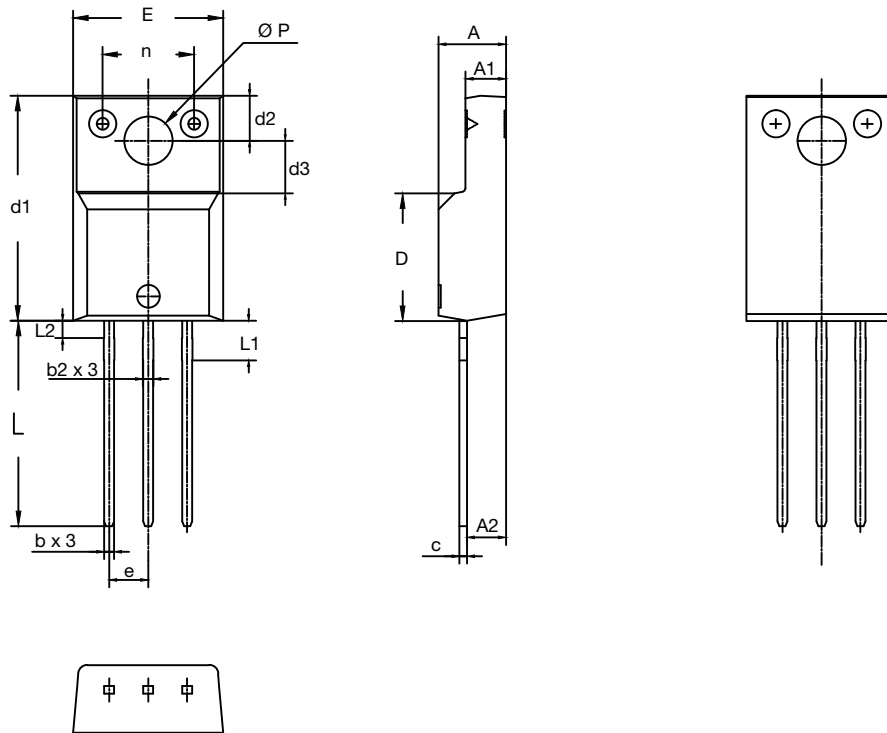


**Normalized Thermal Transient Impedance, Junction-to-Case**

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### TO-220 FULLPAK Thin Lead



SYMBOL	DIMENSIONS			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.30	4.70	0.169	0.185
A1	2.50	2.90	0.098	0.114
A2	2.50	2.70	0.098	0.106
b	0.60	0.80	0.024	0.031
b2	0.60	0.90	0.024	0.035
c	-	0.60	-	0.024
D	8.30	8.70	0.327	0.342
d1	14.70	15.30	0.579	0.602
d2	2.90	3.10	0.114	0.122
d3	3.40	3.60	0.134	0.142
E	9.70	10.30	0.382	0.406
e	2.50	2.70	0.098	0.106
L	13.40	13.80	0.528	0.543
L1	2.50	2.80	0.098	0.110
L2	-	1.20	-	0.047
n	6.05	6.15	0.238	0.242
Ø P	3.00	3.40	0.118	0.134

ECN: T16-0549-Rev. C, 12-Sep-16  
 DWG: 6021



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